

Vishay Semiconductors

High Intensity LED in $\ensuremath{\varnothing}$ 3 mm Tinted Diffused Package

Description

This device has been designed to meet the increasing demand for AlInGaP technology.

It is housed in a 3 mm clear plastic package. The wide viewing angle of these devices provides a high on-off contrast.

All packing units are categorized in luminous intensity groups. That allows users to assemble LEDs with uniform appearance.

Features

- AlInGaP technology
- Standard \varnothing 3 mm (T-1) package
- Small mechanical tolerances
- Suitable for DC and high peak current
- Very wide viewing angle
- Luminous intensity categorized
- Lead-free device



Applications

Status lights OFF / ON indicator Background illumination Readout lights Maintenance lights Legend light

Parts Table

Part	Color, Luminous Intensity	Angle of Half Intensity $(\pm \phi)$	Technology
TLHK4600	Red, $I_V > 6.3 \text{ mcd}$	60 °	AllnGaP on GaAs

Absolute Maximum Ratings

 T_{amb} = 25 °C, unless otherwise specified

TLHK4600

Parameter	Test condition	Symbol	Value	Unit
Reverse voltage		V _R	5	V
DC Forward current	T _{amb} ≤ 60 °C	۱ _F	30	mA
Surge forward current	t _p ≤ 10 μs	I _{FSM}	0.1	A
Power dissipation	T _{amb} ≤ 60 °C	Pv	80	mW
Junction temperature		Tj	100	°C
Operating temperature range		T _{amb}	- 40 to + 100	°C
Storage temperature range		T _{stg}	- 55 to + 100	°C
Soldering temperature	$t \leq 5$ s, 2 mm from body	T _{sd}	260	°C
Thermal resistance junction/ ambient		R _{thJA}	400	K/W

TLHK4600

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Optical and Electrical Characteristics

 $T_{amb} = 25 \ ^{\circ}C$, unless otherwise specified

Red

TLHK4600

Parameter	Test condition	Symbol	Min	Тур.	Max	Unit
Luminous intensity 1)	I _F = 10 mA	I _V	6.3	15		mcd
Dominant wavelength	I _F = 10 mA	λ_d		630		nm
Peak wavelength	I _F = 10 mA	λ _p		643		nm
Angle of half intensity	I _F = 10 mA	φ		± 60		deg
Forward voltage	I _F = 20 mA	V _F		1.9	2.6	V
Junction capacitance	V _R = 0, f = 1 MHz	Cj		15		pF
Reverse voltage	I _R = 10 μA	V _R	5			V

 $^{1)}$ in one Packing Unit $I_{Vmin}/I_{Vmax} \leq 0.5$

Typical Characteristics (T_{amb} = 25 °C unless otherwise specified)



Figure 1. Power Dissipation vs. Ambient Temperature







Figure 3. Rel. Luminous Intensity vs. Angular Displacement



Figure 4. Forward Current vs. Forward Voltage



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Figure 5. Rel. Luminous Intensity vs. Ambient Temperature



Figure 8. Relative Intensity vs. Wavelength



Figure 6. Rel. Lumin. Intensity vs. Forw. Current/Duty Cycle



Figure 7. Relative Luminous Intensity vs. Forward Current

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Package Dimensions in mm





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Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operatingsystems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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